

General Description

- Trench Power AlphaMOS (αMOS LV) technology
- Low $R_{DS(ON)}$
- Low Gate Charge
- High Current Capability
- RoHS and Halogen-Free Compliant

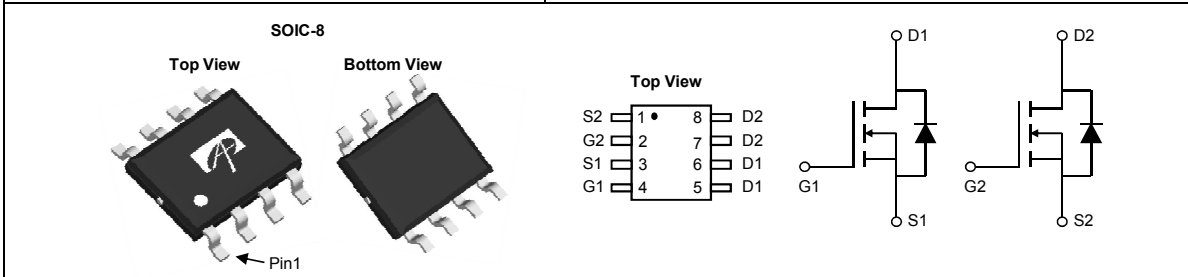
Application

- System switch, inverter

Product Summary

V_{DS}	30V
I_D (at $V_{GS}=10V$)	4.5A
$R_{DS(ON)}$ (at $V_{GS}=10V$)	< 50mΩ
$R_{DS(ON)}$ (at $V_{GS}=4.5V$)	< 68mΩ

100% UIS Tested
100% Rg Tested



Orderable Part Number	Package Type	Form	Minimum Order Quantity
AO4862	SO-8	Tape & Reel	3000

Absolute Maximum Ratings $T_A=25^\circ C$ unless otherwise noted

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	I_D	$T_A=25^\circ C$	4.5
		$T_A=70^\circ C$	3.5
Pulsed Drain Current ^C	I_{DM}	18	A
Avalanche Current ^C	I_{AS}	8	A
Avalanche energy $L=0.1mH$ ^C	E_{AS}	3	mJ
V_{DS} Spike	V_{SPIKE}	36	V
Power Dissipation ^B	P_D	$T_A=25^\circ C$	1.7
		$T_A=70^\circ C$	1.1
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	$^\circ C$

Thermal Characteristics

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient ^A	$R_{\theta JA}$	52	70	$^\circ C/W$
Maximum Junction-to-Ambient ^{A,D}		80	100	$^\circ C/W$
Maximum Junction-to-Lead	$R_{\theta JL}$	35	45	$^\circ C/W$

Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV _{DSS}	Drain-Source Breakdown Voltage	I _D =250μA, V _{GS} =0V	30			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =30V, V _{GS} =0V T _J =55°C			1 5	μA
I _{GSS}	Gate-Body leakage current	V _{DS} =0V, V _{GS} =±20V			±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	1.5	2	2.5	V
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} =10V, I _D =4.5A T _J =125°C		39 63	50 78	mΩ
		V _{GS} =4.5V, I _D =3A		50	68	
g _{FS}	Forward Transconductance	V _{DS} =5V, I _D =4.5A		10		S
V _{SD}	Diode Forward Voltage	I _S =1A, V _{GS} =0V		0.79	1	V
I _S	Maximum Body-Diode Continuous Current				2	A
DYNAMIC PARAMETERS						
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =15V, f=1MHz		200		pF
C _{oss}	Output Capacitance			35		pF
C _{rss}	Reverse Transfer Capacitance			25		pF
R _g	Gate resistance	f=1MHz	1	2	3	Ω
SWITCHING PARAMETERS						
Q _g (10V)	Total Gate Charge	V _{GS} =10V, V _{DS} =15V, I _D =4.5A		4.05	10	nC
Q _g (4.5V)	Total Gate Charge			2	6	nC
Q _{gs}	Gate Source Charge			0.55		nC
Q _{gd}	Gate Drain Charge			1		nC
t _{D(on)}	Turn-On DelayTime	V _{GS} =10V, V _{DS} =15V, R _L =3.3Ω, R _{GEN} =3Ω		4.5		ns
t _r	Turn-On Rise Time			1.5		ns
t _{D(off)}	Turn-Off DelayTime			18.5		ns
t _f	Turn-Off Fall Time			15.5		ns
t _{rr}	Body Diode Reverse Recovery Time	I _F =4.5A, dI/dt=100A/μs		7.5		ns
Q _{rr}	Body Diode Reverse Recovery Charge	I _F =4.5A, dI/dt=100A/μs		2.5		nC

A. The value of R_{θJA} is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with T_A =25° C. The value in any given application depends on the user's specific board design.

B. The power dissipation P_D is based on T_{J(MAX)}=150° C, using ≤ 10s junction-to-ambient thermal resistance.

C. Repetitive rating, pulse width limited by junction temperature T_{J(MAX)}=150° C. Ratings are based on low frequency and duty cycles to keep initial T_J=25° C.

D. The R_{θJA} is the sum of the thermal impedance from junction to lead R_{θJL} and lead to ambient.

E. The static characteristics in Figures 1 to 6 are obtained using <300μs pulses, duty cycle 0.5% max.

F. These curves are based on the junction-to-ambient thermal impedance which is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, assuming a maximum junction temperature of T_{J(MAX)}=150° C. The SOA curve provides a single pulse rating.

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

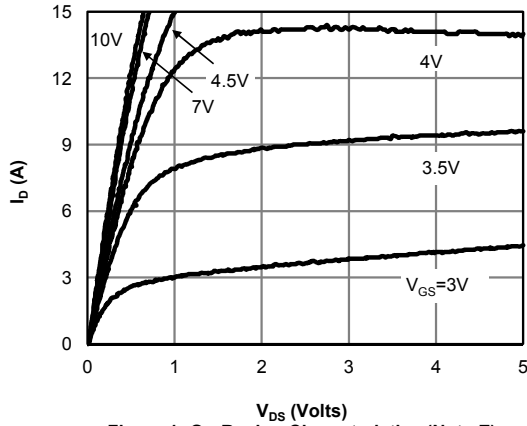


Figure 1: On-Region Characteristics (Note E)

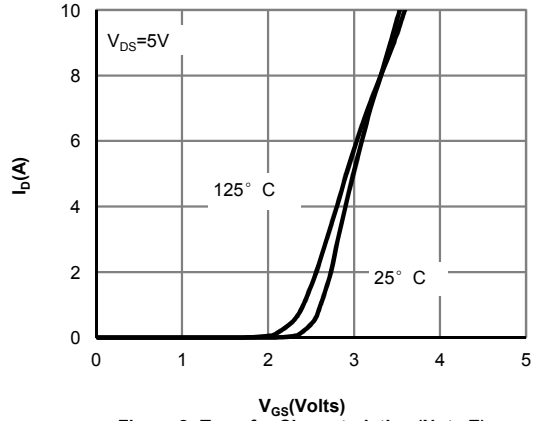


Figure 2: Transfer Characteristics (Note E)

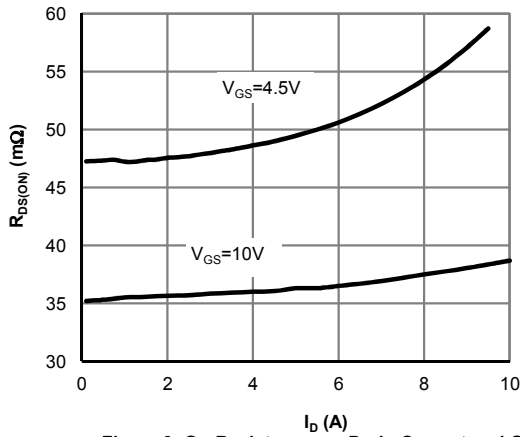


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

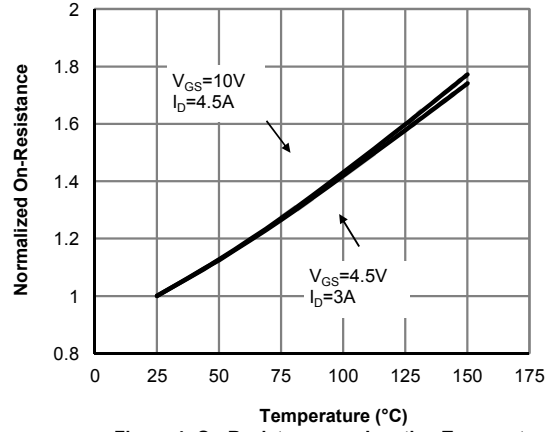


Figure 4: On-Resistance vs. Junction Temperature (Note E)

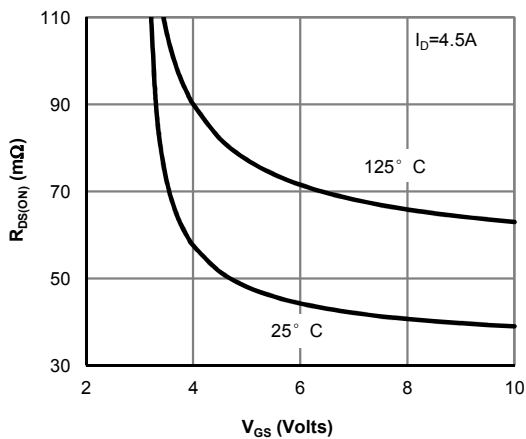


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

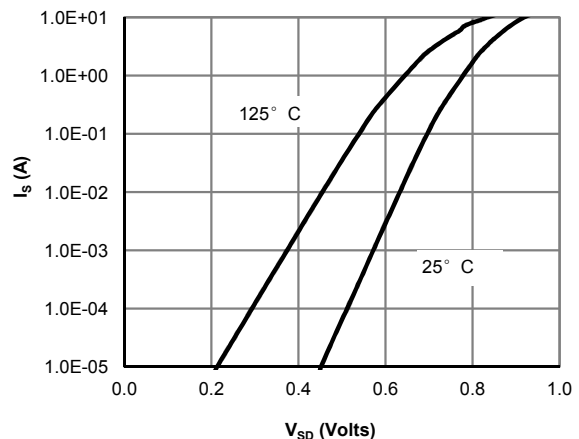


Figure 6: Body-Diode Characteristics (Note E)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

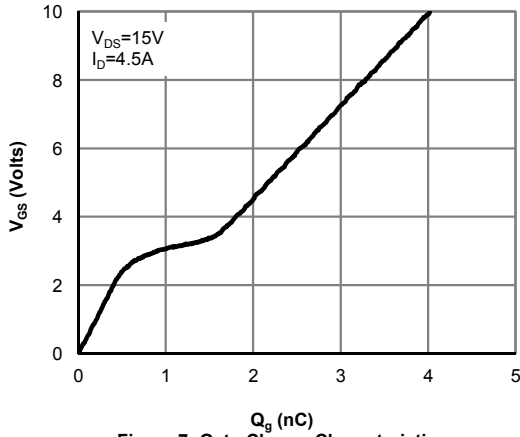


Figure 7: Gate-Charge Characteristics

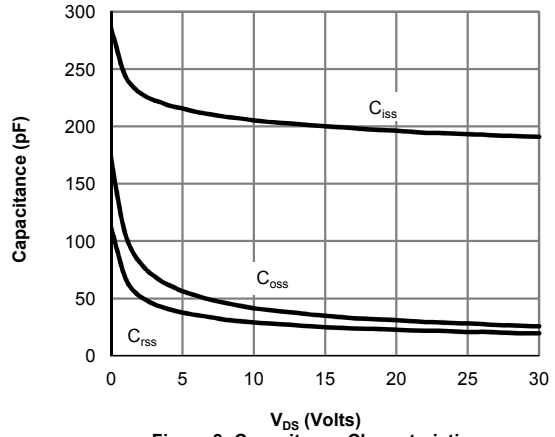


Figure 8: Capacitance Characteristics

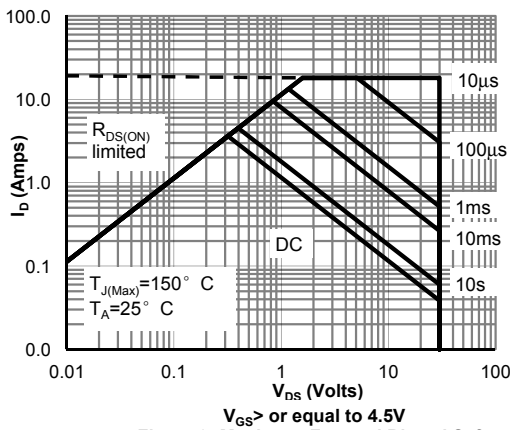


Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

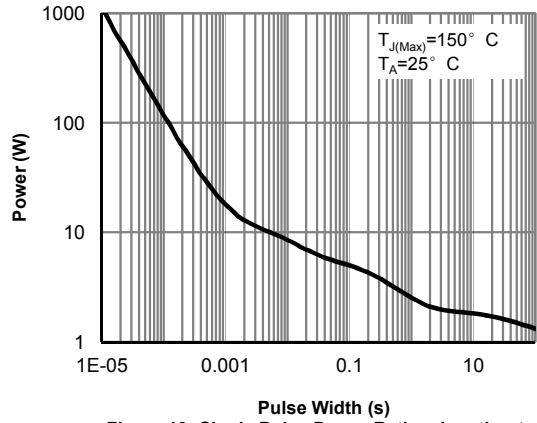


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note F)

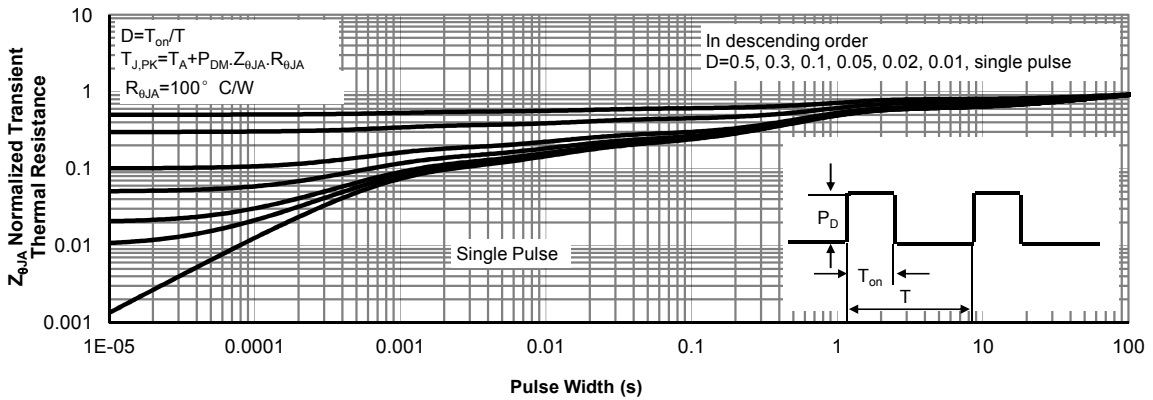
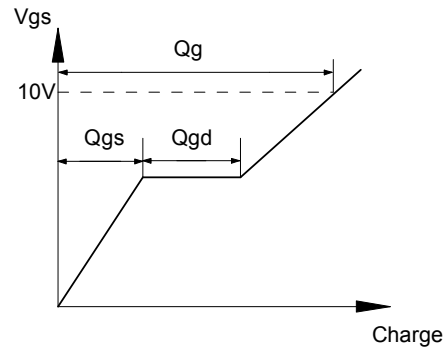
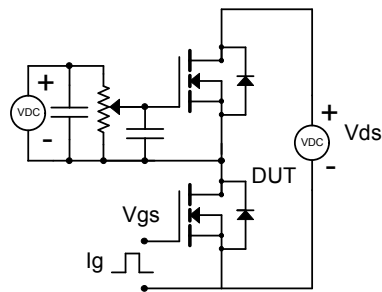
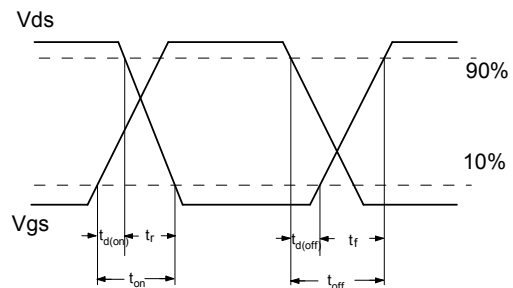
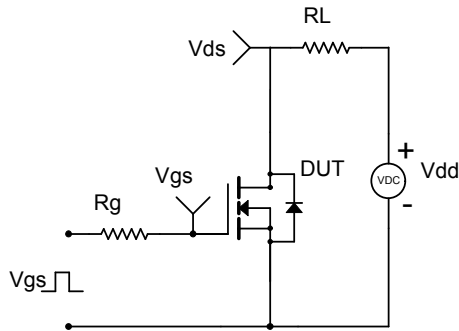


Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)

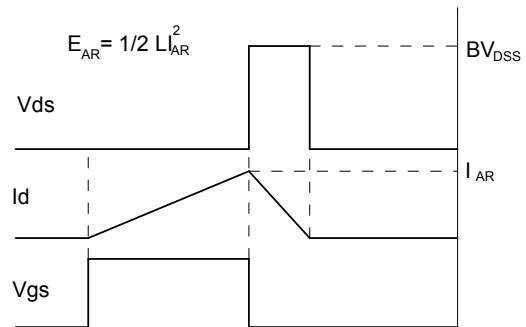
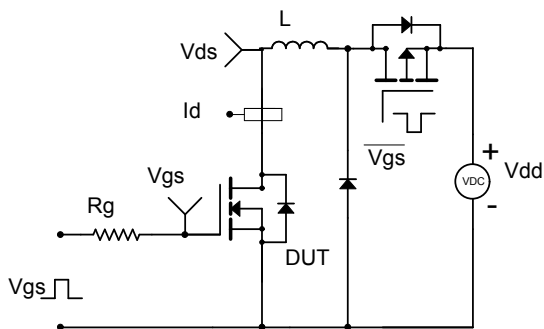
Gate Charge Test Circuit & Waveform



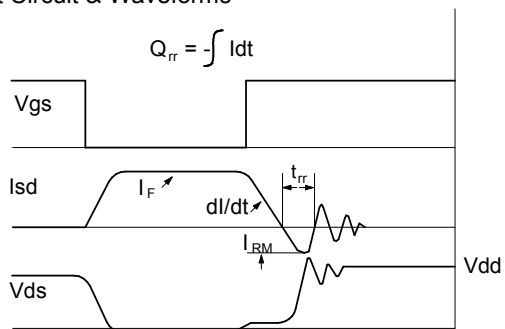
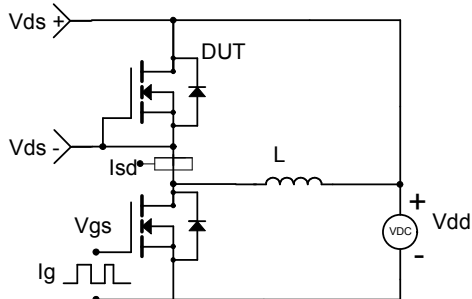
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms



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